

1. Record Nr.	UNINA9910974943003321
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Titolo	Nonvolatile memory design : magnetic, resistive, and phase change // Hai Li, Yiran Chen
Pubbl/distr/stampa	Boca Raton, Fla. : , : CRC Press, , 2012
ISBN	1-315-21830-5 1-351-83419-3 1-280-12159-9 9786613525451 1-4398-0746-9
Edizione	[1st ed.]
Descrizione fisica	1 online resource (200 p.)
Altri autori (Persone)	ChenYiran <1976->
Disciplina	004.568 621.39732
Soggetti	Semiconductor storage devices Magnetic memory (Computers) Flash memories (Computers) Change of state (Physics) - Industrial applications
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	1. Introduction to semiconductor memories -- 2. Phase change memory -- 3. Spin-transfer torque RAM -- 4. Resistive random access memory -- 5. Memristors -- 6. The future of nonvolatile memory.
Sommario/riassunto	The manufacture of flash memory, which is the dominant nonvolatile memory technology, is facing severe technical barriers. So much so, that some emerging technologies have been proposed as alternatives to flash memory in the nano-regime. Nonvolatile Memory Design: Magnetic, Resistive, and Phase Changing introduces three promising candidates: phase-change memory, magnetic random access memory, and resistive random access memory. The text illustrates the fundamental storage mechanism of these technologies and examines their differences from flash memory techniques. Based on the latest advances,